XN01212 (XN1212) Silicon NPN epitaxial planar type

For switching/digital circuits

Composite Transistors

Features

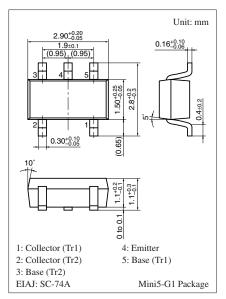
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR2212 (UN2212) × 2

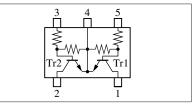
| Absolute Maximum riatings $T_a = 25$ C | | | | | | |
|--|------------------|-------------|------|--|--|--|
| Parameter | Symbol | Rating | Unit | | | |
| Collector-base voltage (Emitter open) | V _{CBO} | 50 | V | | | |
| Collector-emitter voltage (Base open) | V _{CEO} | 50 | V | | | |
| Collector current | I _C | 100 | mA | | | |
| Total power dissipation | P _T | 300 | mW | | | |
| Junction temperature | Tj | 150 | °C | | | |
| Storage temperature | T _{stg} | -55 to +150 | °C | | | |





Marking Symbol: 9K

Internal Connection



| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|---------------------------------|---|------|------|------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$ | 50 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = 50 \text{ V}, I_E = 0$ | | | 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CE} = 50 \text{ V}, I_B = 0$ | | | 0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I _{EBO} | $V_{EB} = 6 V, I_C = 0$ | | | 0.2 | mA |
| Forward current transfer ratio | h _{FE} | $V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$ | 60 | | | |
| h _{FE} Ratio * | h _{FE(Small} | $V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$ | 0.50 | 0.99 | | _ |
| | /Large) | | | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{C} = 10 \text{ mA}, I_{B} = 0.3 \text{ mA}$ | | | 0.25 | V |
| Output voltage high-level | V _{OH} | $V_{CC} = 5 \text{ V}, V_{B} = 0.5 \text{V}, \text{R}_{L} = 1 \text{k}\Omega$ | 4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CC} = 5 \text{ V}, \text{V}_{\text{B}} = 2.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k} \Omega$ | | | 0.2 | V |
| Input resistance | R ₁ | | -30% | 22 | +30% | kΩ |
| Resistance ratio | R ₁ / R ₂ | | 0.8 | 1.0 | 1.2 | |
| Transition frequency | f _T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

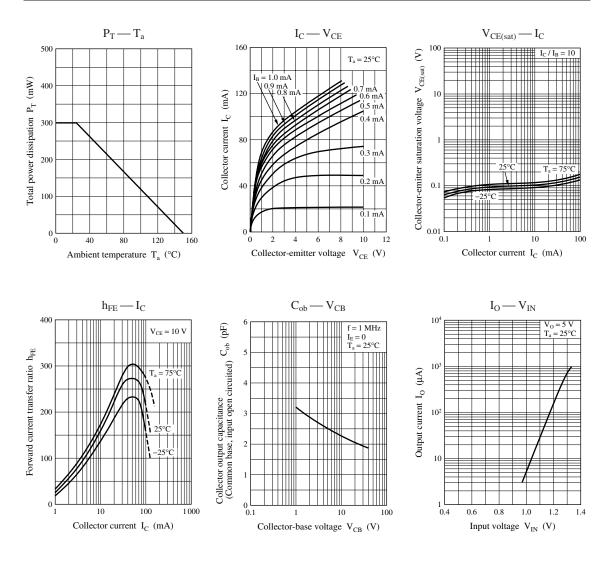
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

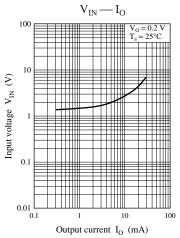
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements www.DataSheet4U.com

Note) The part number in the parenthesis shows conventional part number.

XN01212

Panasonic





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2

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